

N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^{a, e}	Q _g (Typ.)
60	0.026 at V _{GS} = 10 V	26	14.5 nC
	0.040 at V _{GS} = 4.5 V	21	

FEATURES

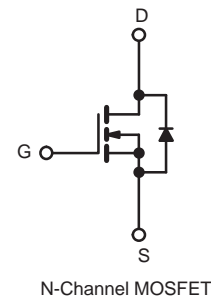
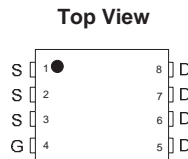
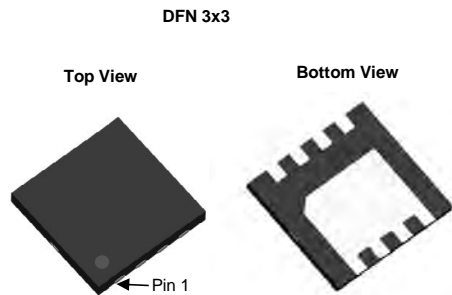
- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested



RoHS
COMPLIANT

APPLICATIONS

- Notebook PC Core
- VRM/POL



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	60	V	
Gate-Source Voltage	V _{GS}	± 20		
Continuous Drain Current (T _J = 175 °C)	I _D	T _C = 25 °C	26 ^{a, e}	
		T _C = 70 °C	21 ^e	
		T _A = 25 °C	10 ^{b, c}	
		T _A = 70 °C	9 ^{b, c}	
Pulsed Drain Current	I _{DM}	80	mJ	
Avalanche Current Pulse	L = 0.1 mH	I _{AS}		20
Single Pulse Avalanche Energy	E _{AS}	10		
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	26 ^{a, e}	
		T _A = 25 °C	16 ^{b, c}	
Maximum Power Dissipation	P _D	T _C = 25 °C	26	
		T _C = 70 °C	17	
		T _A = 25 °C	2.8 ^{b, c}	
		T _A = 70 °C	1.7 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R _{thJA}	38	50	°C/W
Maximum Junction-to-Case	R _{thJC}	3.5	5	

Notes:
a. Based on T_C = 25 °C.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 10 s.
d. Maximum under steady state conditions is 90 °C/W.
e. Calculated based on maximum junction temperature.

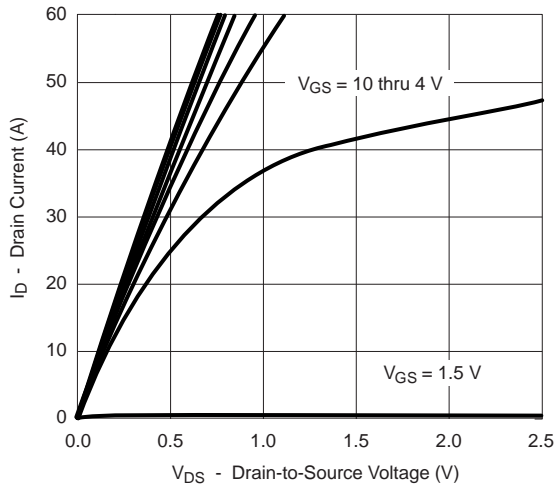
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min .	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		35		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 5.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0		3.0	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	10			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 8\text{ A}$		0.026	0.037	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 8\text{ A}$		0.040	0.056	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 48\text{ V}, I_D = 8\text{ A}$		60		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1100		pF
Output Capacitance	C_{oss}			78		
Reverse Transfer Capacitance	C_{rss}			20		
Total Gate Charge	Q_g	$V_{DS} = 25\text{ V}, V_{GS} = 10\text{ V}, I_D = 8\text{ A}$		14.5		nC
		$V_{DS} = 25\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 8\text{ A}$		11		
Q_{gs}			10			
Q_{gd}			9			
Gate Resistance	R_g	$f = 1\text{ MHz}$		1.4	2.5	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 30\text{ V}, R_L = 0.555\text{ }\Omega$ $I_D \cong 8\text{ A}, V_{GS} = 10\text{ V}, R_g = 1\text{ }\Omega$		12		ns
Rise Time	t_r			9		
Turn-Off Delay Time	$t_{d(off)}$			41		
Fall Time	t_f			10		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 30\text{ V}, R_L = 0.625\text{ }\Omega$ $I_D \cong 8\text{ A}, V_{GS} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		30		
Rise Time	t_r			110		
Turn-Off Delay Time	$t_{d(off)}$			30		
Fall Time	t_f			10		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			26	A
Pulse Diode Forward Current ^a	I_{SM}				80	
Body Diode Voltage	V_{SD}	$I_S = 8\text{ A}$		0.7	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		52		ns
Body Diode Reverse Recovery Charge	Q_{rr}			65		nC
Reverse Recovery Fall Time	t_a			25		ns
Reverse Recovery Rise Time	t_b			23		

Notes:

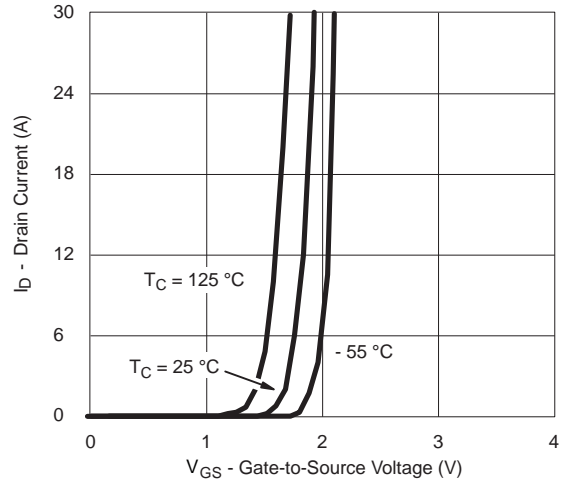
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

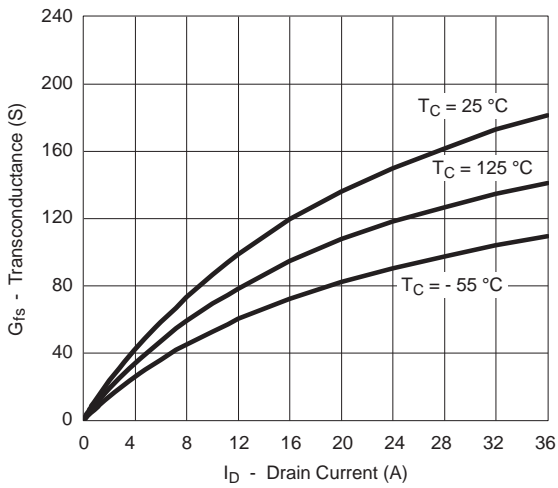
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



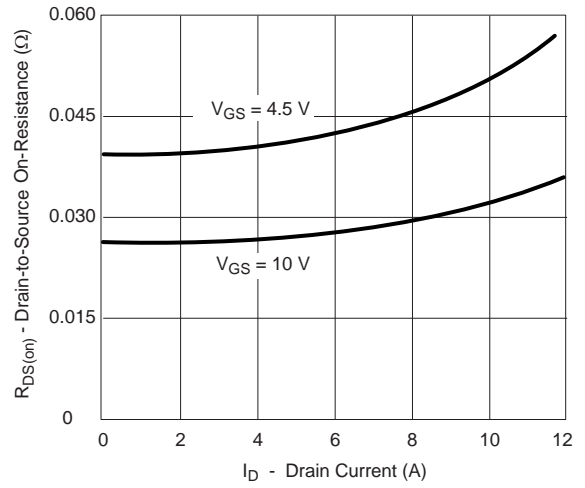
Output Characteristics



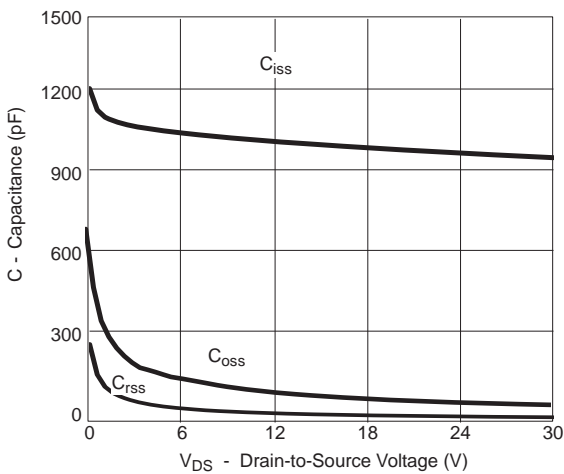
Transfer Characteristics



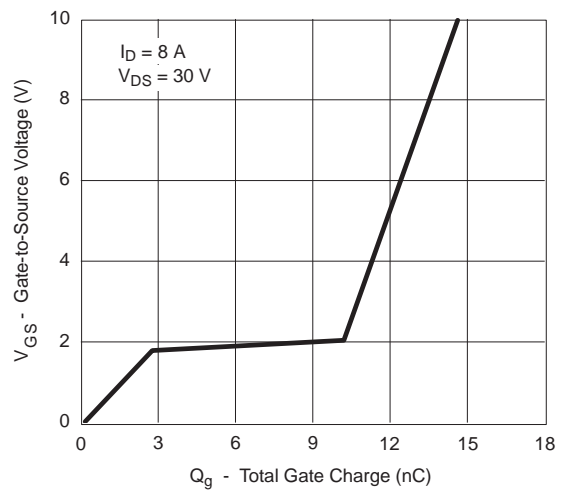
Transconductance



$R_{DS(on)}$ vs. Drain Current

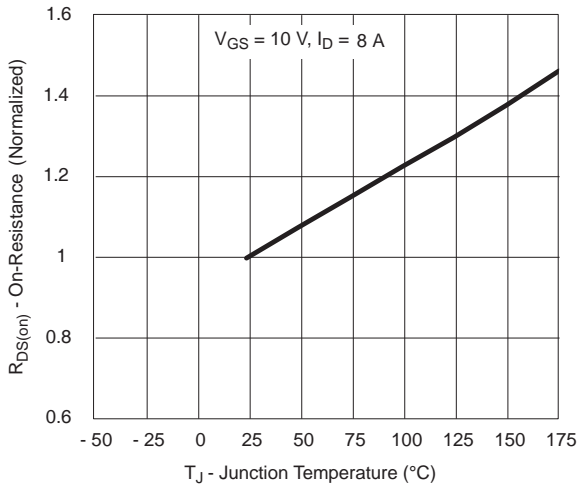


Capacitance

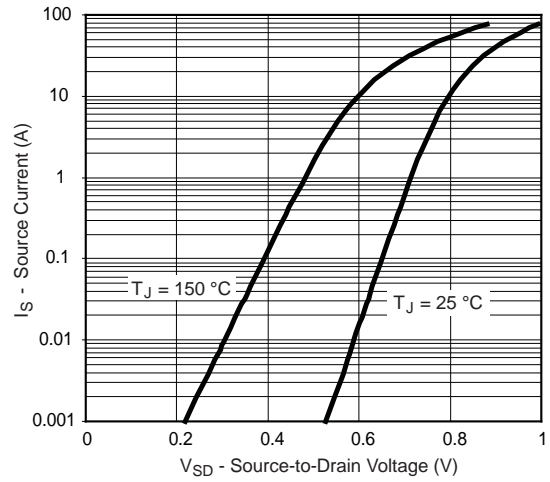


Gate Charge

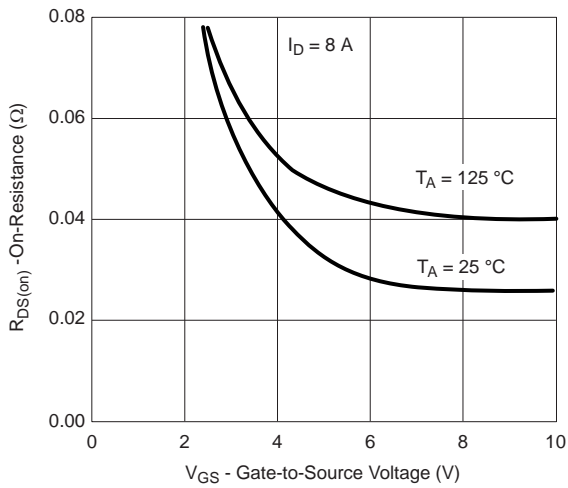
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



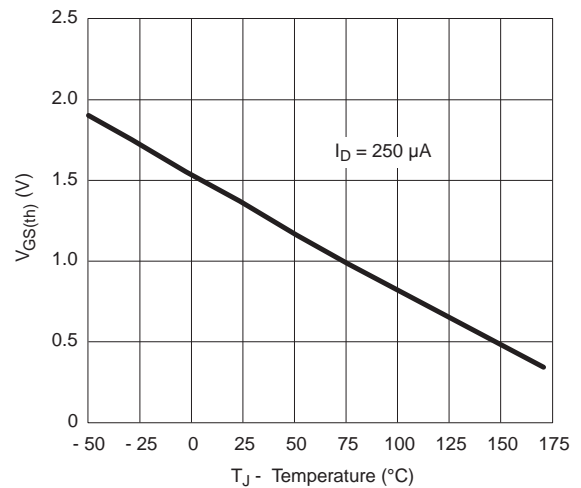
On-Resistance vs. Junction Temperature



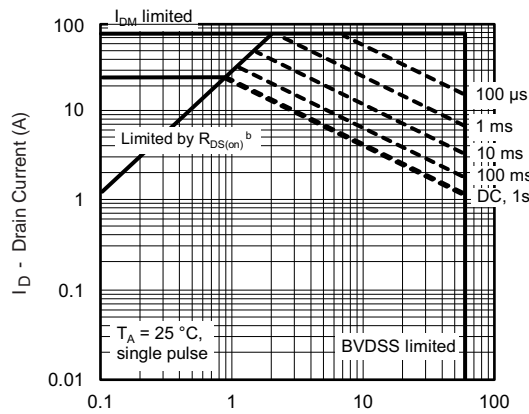
Forward Diode Voltage vs. Temperature



$R_{DS(on)}$ vs. V_{GS} vs. Temperature

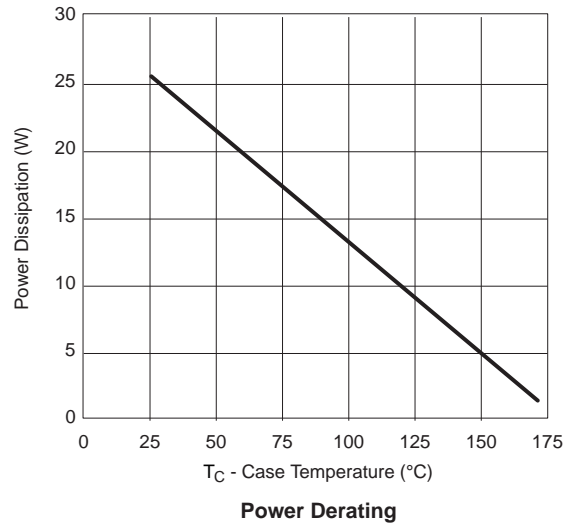
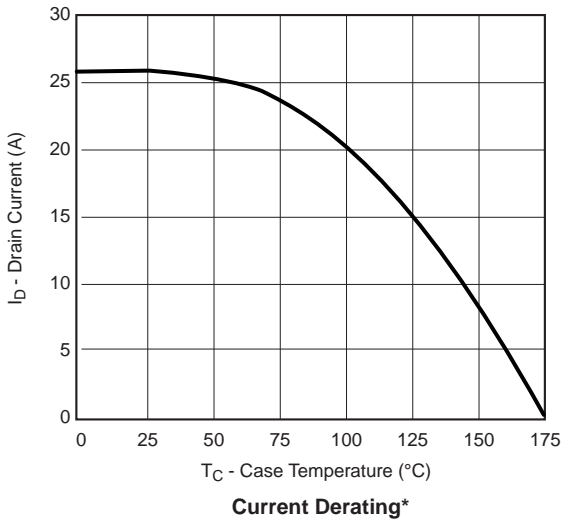


Threshold Voltage

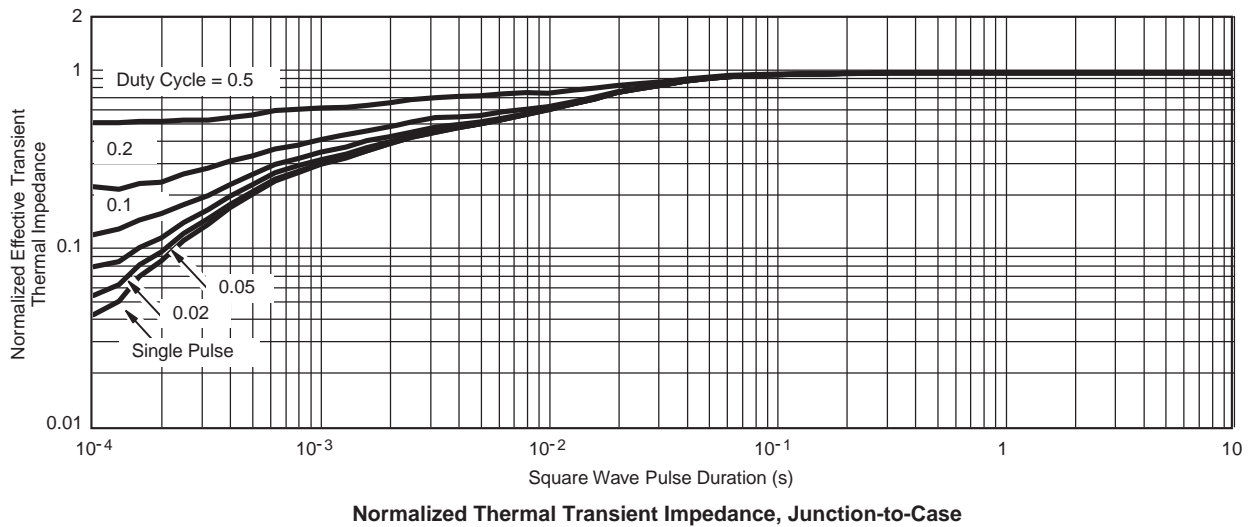


V_{DS} - Drain-to-Source Voltage (V)
* $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Ambient

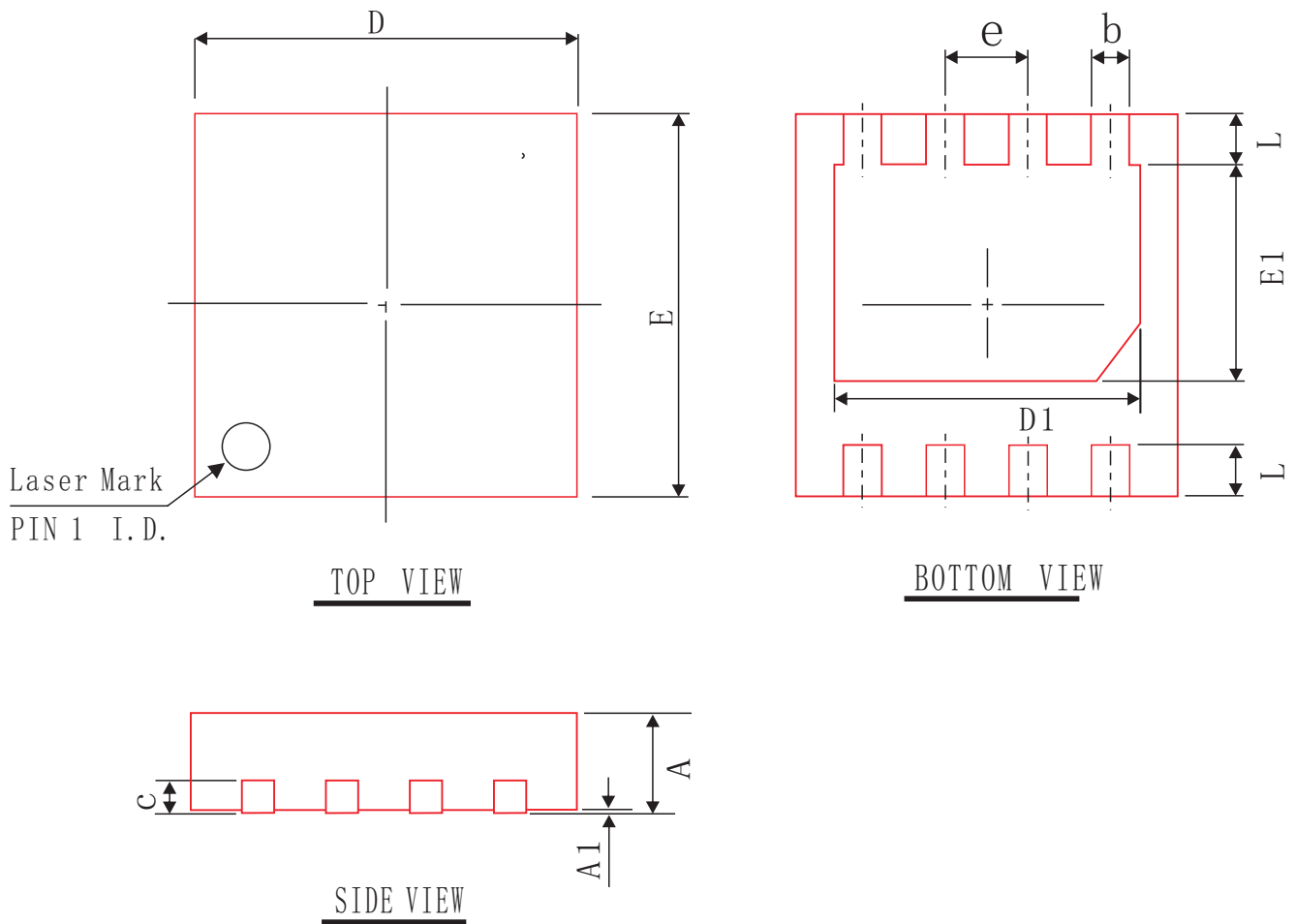
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



* The power dissipation P_D is based on $T_{J(max)} = 175$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



DFN3X3_8L PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
b	0.25	0.30	0.35
D	2.95	3.00	3.07
E	2.95	3.00	3.07
D1	2.30	2.40	2.50
E1	1.60	1.70	1.80
L	0.30	0.40	0.50
c	0.203 REF		
e	0.65 BSC		

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